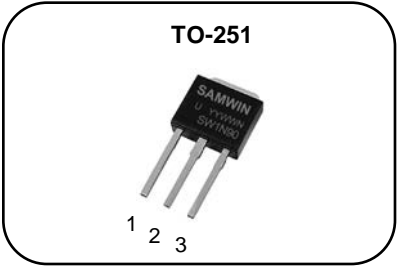


N-channel Enhancement mode TO-251 MOSFET

Features

- High ruggedness
- $R_{DS(ON)}$  (Typ 11.7Ω) @  $V_{GS}=10V$
- Gate Charge (Typ 7nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application: LED, Charger



1. Gate 2. Drain 3. Source

$BV_{DSS} : 900V$   
 $I_D : 1A$   
 $R_{DS(ON)} : 11.7\Omega$

General Description

This power MOSFET is produced with advanced technology of SAMWIN. This technology enable power MOSFET to have better characteristics, such as fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.



Order Codes

| Item | Sales Type | Marking | Package | Packaging |
|------|------------|---------|---------|-----------|
| 1    | SW I 1N90U | SW1N90U | TO-251  | TUBE      |

Absolute maximum ratings

| Symbol         | Parameter  | Value       | Unit |
|----------------|--|-------------|------|
| $V_{DSS}$      | Drain to Source Voltage  | 900         | V    |
| $I_D$          | Continuous Drain Current (@ $T_C=25^{\circ}C$ )                              | 1*          | A    |
|                | Continuous Drain Current (@ $T_C=100^{\circ}C$ )                             | 0.63*       | A    |
| $I_{DM}$       | Drain current pulsed (note 1)  | 4           | A    |
| $V_{GS}$       | Gate to Source Voltage   | ±30         | V    |
| $E_{AS}$       | Single pulsed Avalanche Energy (note 2)                                      | 80          | mJ   |
| $E_{AR}$       | Repetitive Avalanche Energy (note 1)   | 14          | mJ   |
| dv/dt          | Peak diode Recovery dv/dt (note 3)   | 5           | V/ns |
| $P_D$          | Total power dissipation (@ $T_C=25^{\circ}C$ )                               | 83          | W    |
|                | Derating Factor above 25°C   | 0.7         | W/°C |
| $T_{STG}, T_J$ | Operating Junction Temperature & Storage Temperature                         | -55 ~ + 150 | °C   |
| $T_L$          | Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds. | 300         | °C   |

\*. Drain current is limited by junction temperature.

Thermal characteristics

| Symbol     | Parameter                               | Value | Unit |
|------------|---|-------|------|
| $R_{thjc}$ | Thermal resistance, Junction to case    | 1.5   | °C/W |
| $R_{thcs}$ | Thermal resistance, Case to Sink        | 0.5   | °C/W |
| $R_{thja}$ | Thermal resistance, Junction to ambient | 98    | °C/W |

## Electrical characteristic ( $T_C = 25^{\circ}\text{C}$ unless otherwise specified )

| Symbol                         | Parameter                                 | Test conditions                                     | Min. | Typ. | Max. | Unit                 |
|--------------------------------|---|---|------|------|------|----------------------|
| <b>Off characteristics</b>     |   |   |      |      |      |                      |
| $BV_{DSS}$                     | Drain to source breakdown voltage         | $V_{GS}=0V, I_D=250\mu A$                           | 900  |      |      | V                    |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown voltage temperature coefficient | $I_D=250\mu A$ , referenced to $25^{\circ}\text{C}$ |      | 0.74 |      | $V/^{\circ}\text{C}$ |
| $I_{DSS}$                      | Drain to source leakage current           | $V_{DS}=900V, V_{GS}=0V$                            |      |      | 1    | $\mu A$              |
|                                |   | $V_{DS}=720V, T_C=125^{\circ}\text{C}$              |      |      | 50   | $\mu A$              |
| $I_{GSS}$                      | Gate to source leakage current, forward   | $V_{GS}=30V, V_{DS}=0V$                             |      |      | 100  | nA                   |
|                                | Gate to source leakage current, reverse   | $V_{GS}=-30V, V_{DS}=0V$                            |      |      | -100 | nA                   |
| <b>On characteristics</b>      |   |   |      |      |      |                      |
| $V_{GS(TH)}$                   | Gate threshold voltage                    | $V_{DS}=V_{GS}, I_D=250\mu A$                       | 3    |      | 5    | V                    |
| $R_{DS(ON)}$                   | Drain to source on state resistance       | $V_{GS}=10V, I_D=0.5A$                              |      | 11.7 | 16   | $\Omega$             |
| $G_{fs}$                       | Forward Transconductance                  | $V_{DS}=30V, I_D=0.5A$                              |      | 1.2  |      | S                    |
| <b>Dynamic characteristics</b> |   |   |      |      |      |                      |
| $C_{iss}$                      | Input capacitance                         | $V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$              |      | 242  |      | pF                   |
| $C_{oss}$                      | Output capacitance                        |   |      | 31   |      |                      |
| $C_{rss}$                      | Reverse transfer capacitance              |   |      | 11   |      |                      |
| $t_{d(on)}$                    | Turn on delay time                        | $V_{DS}=450V, I_D=1A, R_G=25\Omega$<br>(note 4 , 5) |      | 9    |      | nS                   |
| $t_r$                          | Rising time                               |   |      | 22.5 |      |                      |
| $t_{d(off)}$                   | Turn off delay time                       |   |      | 19.5 |      |                      |
| $t_f$                          | Fall time                                 |   |      | 30   |      |                      |
| $Q_g$                          | Total gate charge                         | $V_{DS}=500V, V_{GS}=10V, I_D=1A$<br>(note 4 , 5)   |      | 7    |      | nC                   |
| $Q_{gs}$                       | Gate-source charge                        |   |      | 1.2  |      |                      |
| $Q_{gd}$                       | Gate-drain charge                         |   |      | 4.4  |      |                      |

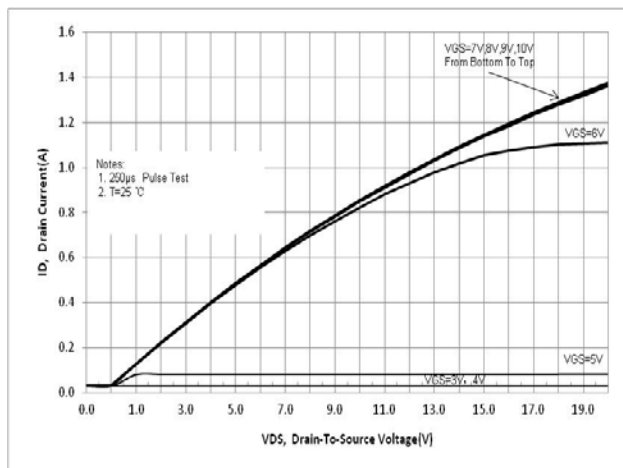
## Source to drain diode ratings characteristics

| Symbol   | Parameter                   | Test conditions                                   | Min. | Typ. | Max. | Unit |
|----------|-----------------------------|---|------|------|------|------|
| $I_S$    | Continuous source current   | Integral reverse p-n Junction diode in the MOSFET |      |      | 1    | A    |
| $I_{SM}$ | Pulsed source current       |   |      |      | 4    | A    |
| $V_{SD}$ | Diode forward voltage drop. | $I_S=1A, V_{GS}=0V$                               |      |      | 1.4  | V    |
| $T_{rr}$ | Reverse recovery time       | $I_S=1A, V_{GS}=0V,$                              |      | 237  |      | nS   |
| $Q_{rr}$ | Breakdown voltage charge    | $di_f/dt=100A/\mu s$                              |      | 654  |      | nC   |

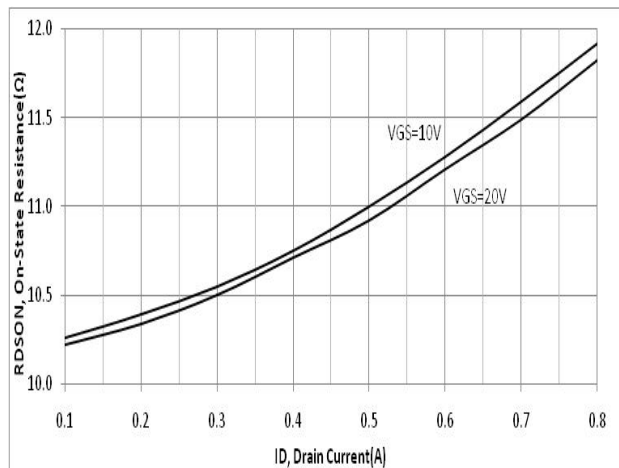
### ※. Notes

1. Repetitive rating : pulse width limited by junction temperature.
2.  $L=160\text{mH}, I_{AS}=1.0A, V_{DD}=100V, R_G=25\Omega$ , Starting  $T_J=25^{\circ}\text{C}$
3.  $I_{SD} \leq 1A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^{\circ}\text{C}$
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature.

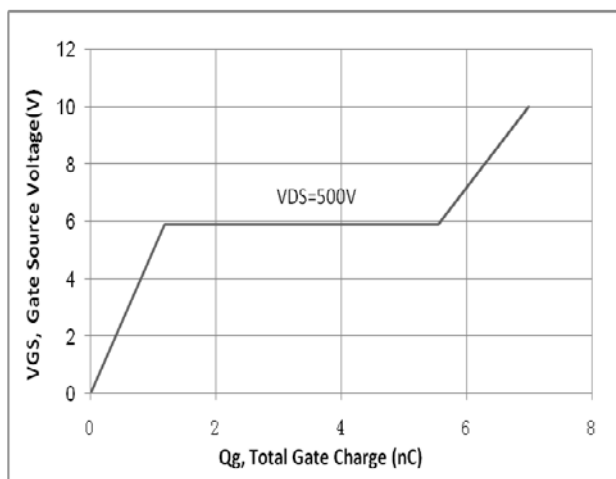
**Fig. 1. On-state characteristics**



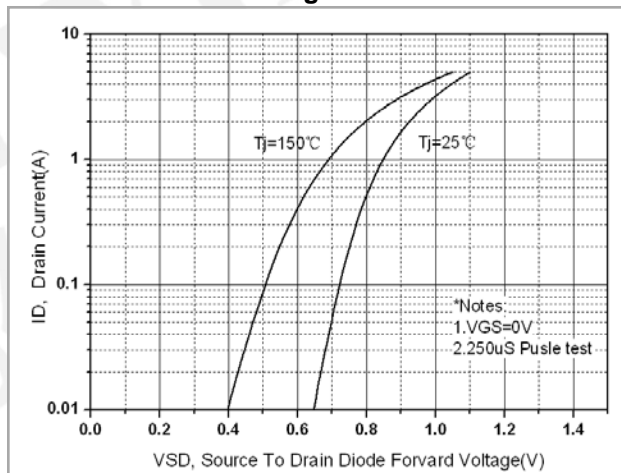
**Fig. 2. On-resistance variation vs. drain current and gate voltage**



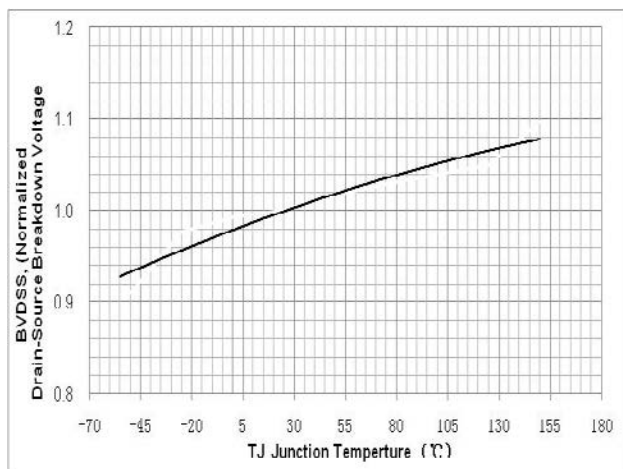
**Fig. 3. Gate charge characteristics**



**Fig. 4. On state current vs. diode forward voltage**



**Fig 5. Breakdown Voltage Variation vs. Junction Temperature**



**Fig. 6. On resistance variation vs. junction temperature**

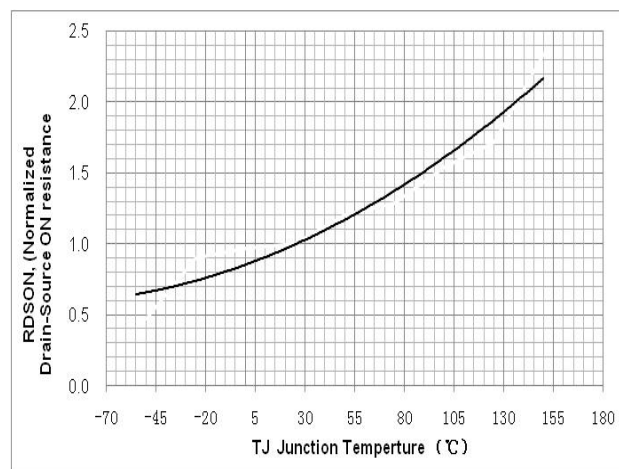


Fig. 7. Maximum safe operating area

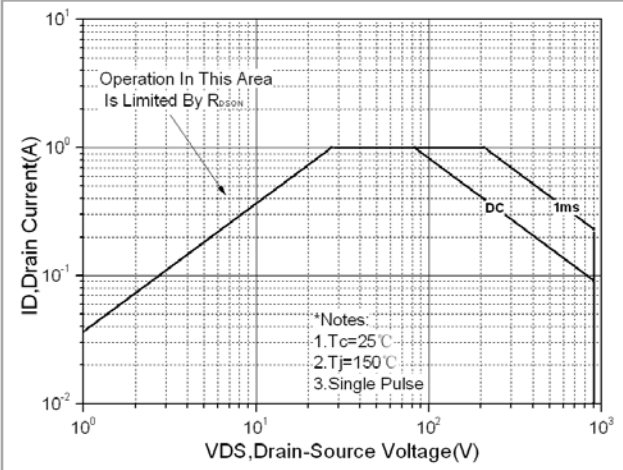


Fig. 8. Transient thermal response curve

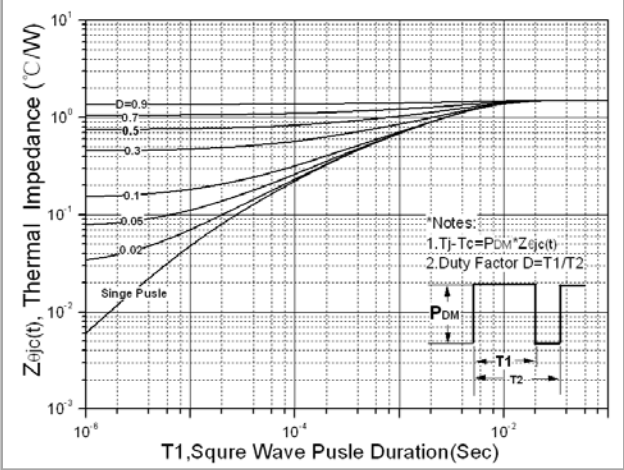


Fig. 9. Capacitance Characteristics

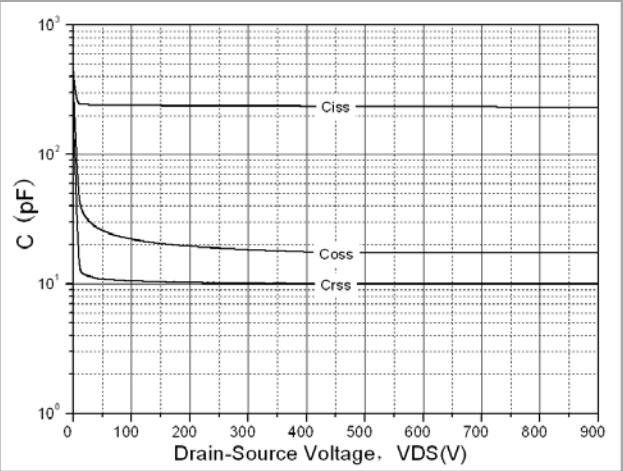


Fig. 10. Gate charge test circuit & waveform

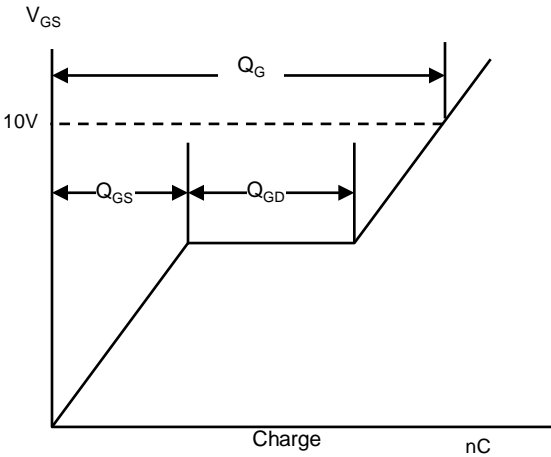
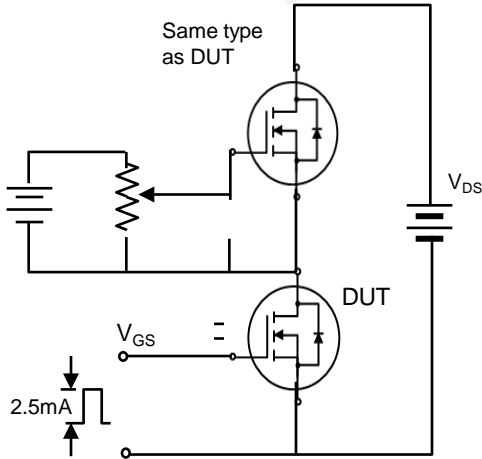


Fig. 11. Switching time test circuit & waveform

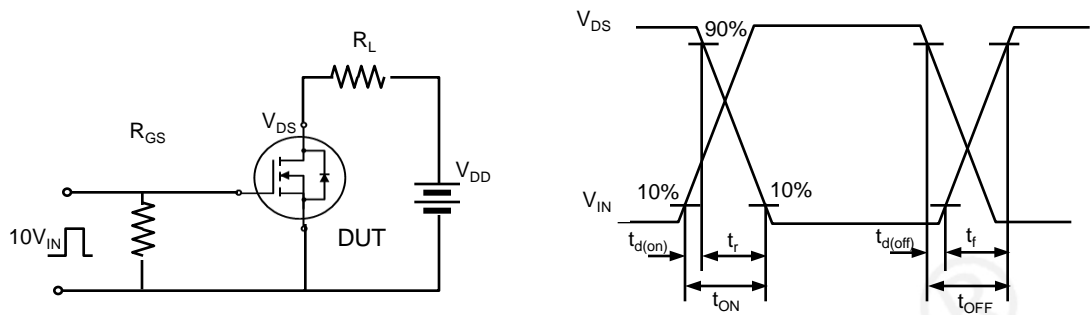


Fig. 12. Unclamped Inductive switching test circuit & waveform

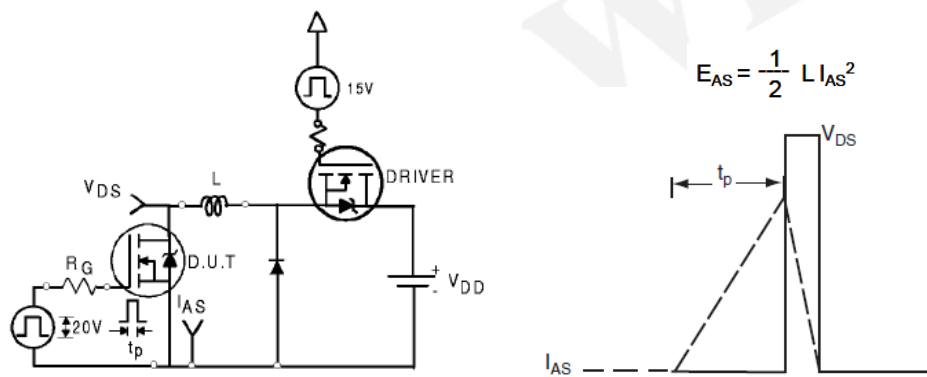
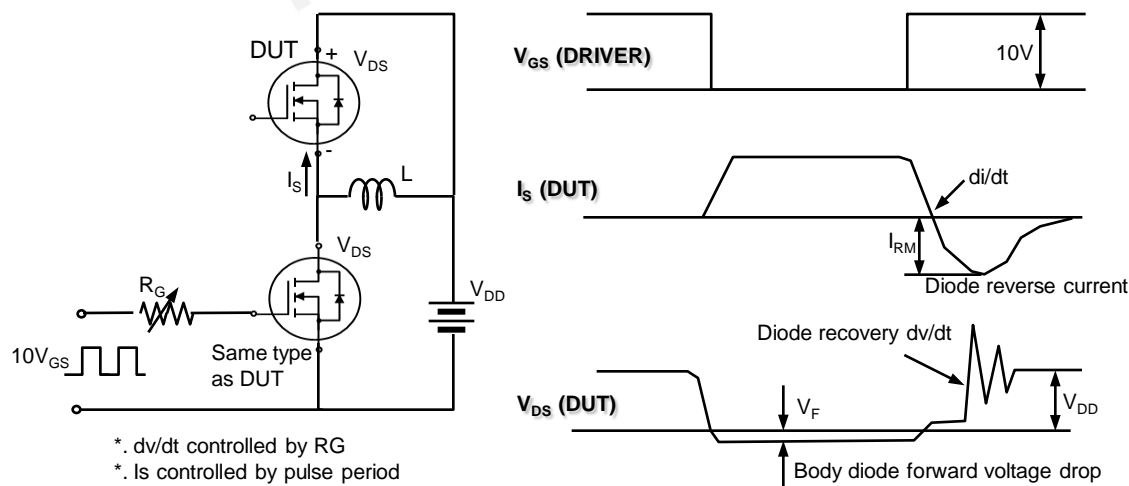



Fig. 13. Peak diode recovery dv/dt test circuit & waveform



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### DISCLAIRATION:

- \* All the data&curve within this document was tested in XI'AN SEMIPOWER TESTING&APPLICATION CENTER.
- \* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
- \* Qualification Standards can also be found on the Web site (<http://www.semipower.com.cn>) 
- \* Any advice, please send your proposal to [samwin@samwinsemi.com](mailto:samwin@samwinsemi.com)